IN THE CLAIMS

Please cancel claims 26, 28, and 29 without prejudice.

Please amend the following claims which are pending in the present application:

1-24. (Cancelled)

25. (Currently amended) A method of forming a transistor comprising:

forming a gate dielectric layer on a layer of semiconductor material having a first lattice with a first structure and a first spacing;

forming a gate electrode on the gate dielectric layer;

implanting dopants into the layer of semiconductor material to form doped tip regions in the layer with a channel between the tip regions;

etching the layer to form source and drain recesses in the layer with the tip regions between the recesses; and

filling the source and drain recesses with a source and a drain respectively, wherein at least one of the source and drain regions is made of a film material which:

(a) is formed epitaxially on the semiconductor material; and

(b) has a second lattice with a second structure which is the same as the first structure; and

(c) includes a dopant selected from one of a p-dopant and an n-dopant, wherein (i) if the dopant is a p-dopant, the second spacing is larger than the first

spacing, and (ii) if the dopant is an n-dopant, the second spacing is smaller than the first spacing.

26. (Cancelled)

27. (Original)   The method of claim 25 wherein the source and drain have a depth into the layer and are spaced by a width from one another, a ratio of the depth to the width being at least 0.12.

28-29.   (Cancelled)

30. (Currently amended)   The method of claim [[28]] 25, wherein the difference between the first spacing and the second spacing creates a stress in the channel.

31. (Currently amended)   The method of claim [[28]] 25, wherein the second material includes the semiconductor material and an additive, the difference between the first spacing and the second spacing being due to the additive.

32. (Previously presented)   The method of claim 31, wherein the semiconductor material is silicon and the additive is selected from one of germanium and carbon.

33. (Previously presented)   The method of claim 32, wherein the additive is germanium.

34. (Previously presented)   The method of claim 33, wherein the germanium comprises between 1 and 20 atomic percent of the silicon and the germanium of the film material.

35. (Currently amended)   The method of claim [[26]] 25, wherein:

(a)   if the dopant of the film material is a p-dopant, the dopants of the tip regions are p-dopants; and

(b)   if the dopant of the film material is an n-dopant, the dopants of the tip regions are n-dopants.

36. (Currently amended)   The method of claim [[26]] 25, wherein the dopant comprises at least $0.5 \times 10^{20}/cm^3$ of the film material.

37. (Previously presented)   The method of claim 36, wherein the film material has a resistivity of less than 1.1mOhm-cm.

38. (Previously presented)   The method of claim 25, wherein the gate dielectric layer is formed before the dopants are implanted.